

RJP4002ASA

Nch IGBT for Strobe Flash

REJ03G1473-0100 Rev.1.00 Oct 13, 2006

Features

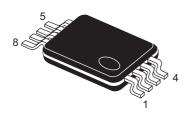
• Small surface mount package (TSSOP-8)

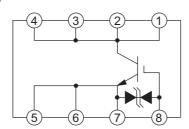
V_{CES}: 400 VI_{CM}: 150 A

• Drive voltage: 2.5 V

Outline

RENESAS Package code: PTSP0008JB-B (Package name: TSSOP-8 <TTP-8DV>)





1, 2, 3, 4 : Collector 5, 6 : Emitter

7 : Emitter

(for the gate drive)

8 : Gate

Note: Pin 7 is for the gate drive only.

Note that current from the main circuit cannot flow into this section. (Please see page 3.)

Applications

Strobe flash for cameras

Maximum Ratings

 $(Tc = 25^{\circ}C)$

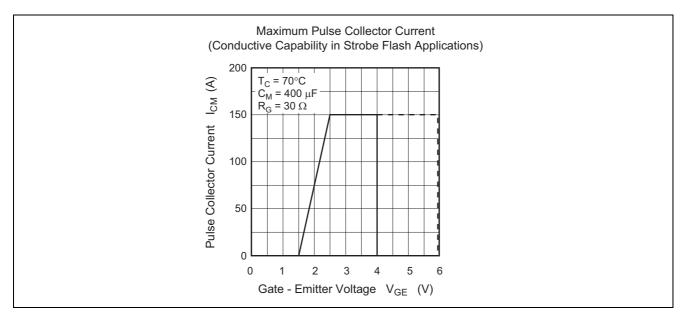
Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V _{CES}	400	V	V _{GE} = 0 V
Gate-emitter voltage	V_{GES}	±4	V	V _{CE} = 0 V
Peak gate-emitter voltage	V_{GEM}	±6	V	$V_{CE} = 0 \text{ V}, \text{ tw} = 10 \text{ s}$
Collector current (Pulse)	I _{CM}	150	Α	C _M = 400 μF
				(see performance curve)
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	

Electrical Characteristics

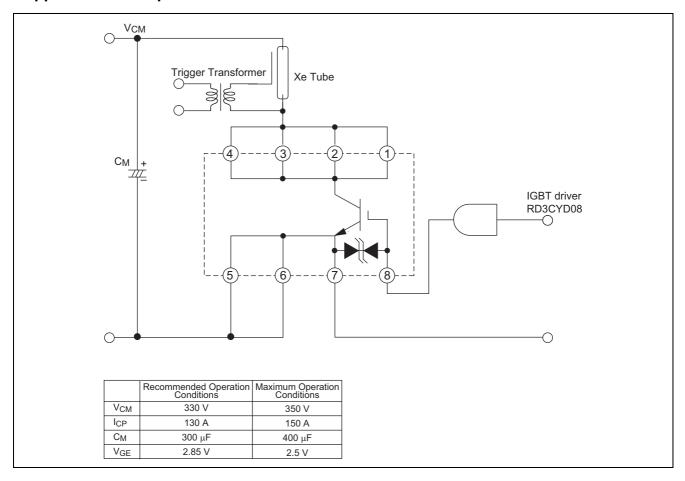
 $(Tj = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	$V_{(BR)CES}$	450	_	_	V	$I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$
Collector-emitter leakage current	I _{CES}	_	_	10	μΑ	$V_{CE} = 400 \text{ V}, V_{GE} = 0 \text{ V}$
Gate-emitter leakage current	I _{GES}	_	_	±10	μΑ	$V_{GE} = \pm 4 \text{ V}, V_{CE} = 0 \text{ V}$
Gate-emitter threshold voltage	$V_{GE(th)}$	0.4	0.6	1.2	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector-emitter saturation voltage	V _{CE(sat)}	_	4.5	9.0	V	I _C = 150 A, V _{GE} = 2.5 V
Input capacitance	Cies	_	6500	_	pF	$V_{CE} = 25 \text{ V}, V_{GE} = 10 \text{ V},$
						f = 1MHz

Performance Curves



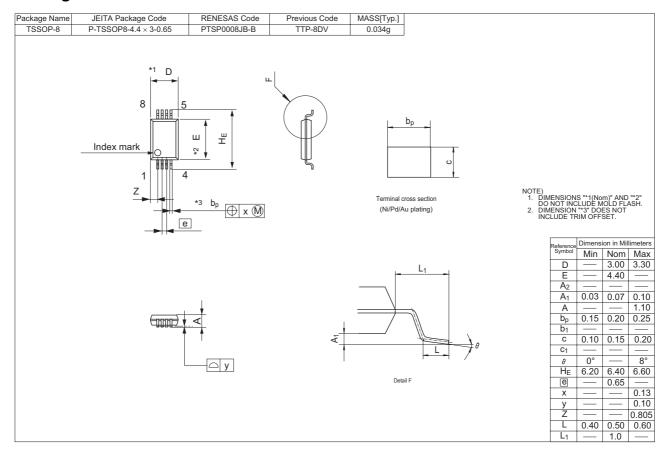
Application Example



Precautions on Usage

- 1. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 2. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And turn-off dv/dt must become less than 400 V/ μs . In general, when $R_{G\,(off)}$ = 30 Ω , it is satisfied.
- 3. The ground of the drive signal must be connected to pin 3 only. If the emitter terminal pins 1 and 2 in which a large currents flow are given to the device as the drive signal emitter, the device may be damaged due to large currents since the specified gate voltage is not applied to the IGBT within the device.
- 4. The operation life should be endured until repeated discharge of 5,000 times under the charge current ($I_{Xe} \le 150 \text{ A}$: full luminescence condition) of main capacitor. Repetition period under full luminescence condition is over 3 seconds
- 5. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours when V_{GE} is driven at 4 V.

Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – 00 – Q0	RJP4002ASA-00-Q0

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect to the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510